

Jingyu Lin

List of Publications by Year in descending order

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404
papers

17,945
citations

¹¹⁶³⁹
70
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¹⁹⁷²⁶
117
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407
all docs

407
docs citations

407
times ranked

12449
citing authors

#	ARTICLE	IF	CITATIONS
1	Deep Ultraviolet Photoluminescence of Water-Soluble Self-Passivated Graphene Quantum Dots. ACS Nano, 2012, 6, 5102-5110.	7.3	1,526
2	Deep Ultraviolet to Near-Infrared Emission and Photoresponse in Layered N-Doped Graphene Quantum Dots. ACS Nano, 2014, 8, 6312-6320.	7.3	455
3	InGaN/GaN multiple quantum well solar cells with long operating wavelengths. Applied Physics Letters, 2009, 94, .	1.5	321
4	III-nitride blue and ultraviolet photonic crystal light emitting diodes. Applied Physics Letters, 2004, 84, 466-468.	1.5	318
5	Band structure and fundamental optical transitions in wurtzite AlN. Applied Physics Letters, 2003, 83, 5163-5165.	1.5	310
6	Unique optical properties of AlGaIn alloys and related ultraviolet emitters. Applied Physics Letters, 2004, 84, 5264-5266.	1.5	303
7	III-Nitride full-scale high-resolution microdisplays. Applied Physics Letters, 2011, 99, .	1.5	270
8	III-nitride blue microdisplays. Applied Physics Letters, 2001, 78, 1303-1305.	1.5	264
9	Mg acceptor level in AlN probed by deep ultraviolet photoluminescence. Applied Physics Letters, 2003, 83, 878-880.	1.5	249
10	Structural phase behavior in II-VI semiconductor nanoparticles. Applied Physics Letters, 1995, 67, 831-833.	1.5	231
11	Fundamental optical transitions in GaN. Applied Physics Letters, 1996, 68, 2784-2786.	1.5	185
12	GaN microdisk light emitting diodes. Applied Physics Letters, 2000, 76, 631-633.	1.5	185
13	InGaN/GaN multiple quantum well concentrator solar cells. Applied Physics Letters, 2010, 97, .	1.5	179
14	Epitaxially grown semiconducting hexagonal boron nitride as a deep ultraviolet photonic material. Applied Physics Letters, 2011, 98, .	1.5	178
15	Nitride micro-LEDs and beyond - a decade progress review. Optics Express, 2013, 21, A475.	1.7	173
16	200nm deep ultraviolet photodetectors based on AlN. Applied Physics Letters, 2006, 89, 213510.	1.5	170
17	Time-resolved photoluminescence studies of $\text{In}_x\text{Ga}_{1-x}\text{As}_y\text{N}_{1-y}$. Applied Physics Letters, 2000, 76, 188-190.	1.5	162
18	Nitride deep-ultraviolet light-emitting diodes with microlens array. Applied Physics Letters, 2005, 86, 173504.	1.5	162

#	ARTICLE	IF	CITATIONS
19	Deep impurity transitions involving cation vacancies and complexes in AlGa _N alloys. Applied Physics Letters, 2005, 86, 222108.	1.5	160
20	Metastability and persistent photoconductivity in Mg-doped p-type GaN. Applied Physics Letters, 1996, 68, 1808-1810.	1.5	154
21	Development of microLED. Applied Physics Letters, 2020, 116, .	1.5	152
22	Photoluminescence studies of impurity transitions in Mg-doped AlGa _N alloys. Applied Physics Letters, 2009, 94, .	1.5	150
23	Optical and electrical properties of Mg-doped p-type Al _x Ga _{1-x} N. Applied Physics Letters, 2002, 80, 1210-1212.	1.5	149
24	Temperature and compositional dependence of the energy band gap of AlGa _N alloys. Applied Physics Letters, 2005, 87, 242104.	1.5	147
25	Nature of Mg impurities in GaN. Applied Physics Letters, 1996, 69, 1474-1476.	1.5	145
26	Dependence of Ni/AlGa _N Schottky barrier height on Al mole fraction. Journal of Applied Physics, 2000, 87, 801-804.	1.1	140
27	Structure and Photoluminescence Study of TiO ₂ Nanoneedle Texture along Vertically Aligned Carbon Nanofiber Arrays. Journal of Physical Chemistry C, 2008, 112, 17127-17132.	1.5	135
28	Enhanced light extraction in III-nitride ultraviolet photonic crystal light-emitting diodes. Applied Physics Letters, 2004, 85, 142-144.	1.5	134
29	III-nitride photonic crystals. Applied Physics Letters, 2003, 83, 1231-1233.	1.5	131
30	Mechanisms of band-edge emission in Mg-doped p-type GaN. Applied Physics Letters, 1996, 68, 1883-1885.	1.5	130
31	InGa _N /Ga _N quantum well interconnected microdisk light emitting diodes. Applied Physics Letters, 2000, 77, 3236-3238.	1.5	123
32	Correlation between optoelectronic and structural properties and epilayer thickness of AlN. Applied Physics Letters, 2007, 90, 241101.	1.5	123
33	Hydrogen generation by solar water splitting using p-InGa _N photoelectrochemical cells. Applied Physics Letters, 2010, 96, .	1.5	123
34	Time-resolved photoluminescence studies of Al _x Ga _{1-x} N alloys. Applied Physics Letters, 2000, 76, 1252-1254.	1.5	121
35	Hexagonal boron nitride for deep ultraviolet photonic devices. Semiconductor Science and Technology, 2014, 29, 084003.	1.0	121
36	Photoluminescence studies of impurity transitions in AlGa _N alloys. Applied Physics Letters, 2006, 89, 092107.	1.5	119

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37	Dielectric strength, optical absorption, and deep ultraviolet detectors of hexagonal boron nitride epilayers. Applied Physics Letters, 2012, 101, .	1.5	118
38	Electrical and optical properties of Mg-doped Al _{0.7} Ga _{0.3} N alloys. Applied Physics Letters, 2005, 86, 092108.	1.5	117
39	Enhanced p-type conduction in GaN and AlGa _{1-x} N by Mg ²⁺ -doping. Applied Physics Letters, 2003, 82, 3041-3043.	1.5	116
40	Transport properties of highly conductive n-type Al-rich Al _x Ga _{1-x} N (x ≈ 0.7). Applied Physics Letters, 2004, 85, 3769-3771.	1.5	116
41	Correlation between optical and electrical properties of Mg-doped AlN epilayers. Applied Physics Letters, 2006, 89, 152120.	1.5	113
42	Quantum-confined Stark effects in semiconductor quantum dots. Physical Review B, 1995, 52, 5913-5922.	1.1	107
43	III-nitride micro-emitter arrays: development and applications. Journal Physics D: Applied Physics, 2008, 41, 094001.	1.3	107
44	Persistent photoconductivity in a two-dimensional electron gas system formed by an AlGa _{1-x} N/GaN heterostructure. Journal of Applied Physics, 1997, 82, 1227-1230.	1.1	105
45	Thermoelectric properties of In _x Ga _{1-x} N alloys. Applied Physics Letters, 2008, 92, .	1.5	105
46	Hexagonal boron nitride epitaxial layers as neutron detector materials. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2011, 654, 417-420.	0.7	105
47	Time-resolved photoluminescence studies of InGa _{1-x} N epilayers. Applied Physics Letters, 1996, 69, 2837-2839.	1.5	101
48	Piezoelectric effects on the optical properties of GaN/Al _x Ga _{1-x} N multiple quantum wells. Applied Physics Letters, 1998, 73, 3426-3428.	1.5	101
49	Polarization of III-nitride blue and ultraviolet light-emitting diodes. Applied Physics Letters, 2005, 86, 091107.	1.5	99
50	Optical and electrical properties of Al-rich AlGa _{1-x} N alloys. Applied Physics Letters, 2001, 79, 3245-3247.	1.5	94
51	Nature of deep center emissions in GaN. Applied Physics Letters, 2010, 96, .	1.5	94
52	Effects of tensile and compressive strain on the luminescence properties of AlInGa _{1-x} N/InGa _{1-x} N quantum well structures. Applied Physics Letters, 2000, 77, 821-823.	1.5	93
53	Epitaxial growth and demonstration of hexagonal BN/AlGa _{1-x} N p-n junctions for deep ultraviolet photonics. Applied Physics Letters, 2012, 100, .	1.5	93
54	Recent developments of wide-bandgap semiconductor based UV sensors. Diamond and Related Materials, 2009, 18, 860-864.	1.8	92

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55	Band-edge photoluminescence of AlN epilayers. Applied Physics Letters, 2002, 81, 3365-3367.	1.5	91
56	Deep ultraviolet picosecond time-resolved photoluminescence studies of AlN epilayers. Applied Physics Letters, 2003, 82, 1694-1696.	1.5	90
57	Relaxation of persistent photoconductivity in Al _{0.3} Ga _{0.7} As. Physical Review B, 1990, 42, 5855-5858.	1.1	88
58	Percolation transition of persistent photoconductivity in II-VI mixed crystals. Physical Review Letters, 1990, 64, 2547-2550.	2.9	86
59	Quantum shift of band-edge stimulated emission in InGaN/GaN multiple quantum well light-emitting diodes. Applied Physics Letters, 1997, 70, 2978-2980.	1.5	85
60	Direct hydrogen gas generation by using InGaN epilayers as working electrodes. Applied Physics Letters, 2008, 93, .	1.5	85
61	AlGaN-based ultraviolet light-emitting diodes grown on AlN epilayers. Applied Physics Letters, 2004, 85, 4777-4779.	1.5	83
62	A study of the Au/Ni ohmic contact on p-GaN. Journal of Applied Physics, 2000, 88, 4196.	1.1	82
63	Excitonic recombination in GaN grown by molecular beam epitaxy. Applied Physics Letters, 1995, 67, 3387-3389.	1.5	76
64	Al _x Ga _{1-x} N/GaN band offsets determined by deep-level emission. Journal of Applied Physics, 2001, 90, 1887-1890.	1.1	76
65	The origin of deep-level impurity transitions in hexagonal boron nitride. Applied Physics Letters, 2015, 106, .	1.5	76
66	Realization of highly efficient hexagonal boron nitride neutron detectors. Applied Physics Letters, 2016, 109, .	1.5	75
67	Achieving highly conductive AlGaN alloys with high Al contents. Applied Physics Letters, 2002, 81, 1038-1040.	1.5	74
68	Growth and optical properties of In _x Al _y Ga _{1-x-y} N quaternary alloys. Applied Physics Letters, 2001, 78, 61-63.	1.5	72
69	Growth of III-nitride photonic structures on large area silicon substrates. Applied Physics Letters, 2006, 88, 171909.	1.5	72
70	Two-dimensional excitons in three-dimensional hexagonal boron nitride. Applied Physics Letters, 2013, 103, .	1.5	72
71	Band-edge exciton states in AlN single crystals and epitaxial layers. Applied Physics Letters, 2004, 85, 4334.	1.5	70
72	Electroluminescent properties of erbium-doped III-N light-emitting diodes. Applied Physics Letters, 2004, 84, 1061-1063.	1.5	69

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73	Electrical and optical properties of p-type InGaN. Applied Physics Letters, 2009, 95, .	1.5	66
74	Optical transitions in GaN/Al _x Ga _{1-x} N multiple quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 1996, 69, 2453-2455.	1.5	65
75	Optical modes within III-nitride multiple quantum well microdisk cavities. Applied Physics Letters, 1998, 72, 1530-1532.	1.5	65
76	GaN-based waveguide devices for long-wavelength optical communications. Applied Physics Letters, 2003, 82, 1326-1328.	1.5	64
77	Review—Hexagonal Boron Nitride Epilayers: Growth, Optical Properties and Device Applications. ECS Journal of Solid State Science and Technology, 2017, 6, Q3012-Q3021.	0.9	64
78	Neutral—donor—bound exciton recombination dynamics in GaN grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1995, 67, 1653-1655.	1.5	62
79	Fabrication of n-type nickel doped B5C1+I ⁺ homojunction and heterojunction diodes. Applied Physics Letters, 1997, 70, 1028-1030.	1.5	62
80	Optical properties of AlN and GaN in elevated temperatures. Applied Physics Letters, 2004, 85, 3489-3491.	1.5	62
81	Effects of well thickness and Si doping on the optical properties of GaN/AlGa _N multiple quantum wells. Applied Physics Letters, 1997, 71, 1368-1370.	1.5	61
82	Exciton-phonon interaction in InGa _N /Ga _N and GaN/AlGa _N multiple quantum wells. Applied Physics Letters, 1997, 70, 2882-2884.	1.5	61
83	III-nitride ultraviolet light-emitting diodes with delta doping. Applied Physics Letters, 2003, 83, 566-568.	1.5	60
84	Exciton localization in AlGa _N alloys. Applied Physics Letters, 2006, 88, 062103.	1.5	60
85	Optical resonance modes in GaN pyramid microcavities. Applied Physics Letters, 1999, 75, 763-765.	1.5	59
86	Persistent photoconductivity in Ga _{1-x} In _x NyAs _{1-y} . Applied Physics Letters, 1999, 75, 1899-1901.	1.5	58
87	Properties of Co-, Cr-, or Mn-implanted AlN. Journal of Applied Physics, 2003, 94, 1592-1596.	1.1	58
88	Room temperature intrinsic optical transition in GaN epilayers: The band-to-band versus excitonic transitions. Applied Physics Letters, 1997, 71, 635-637.	1.5	57
89	Erbium-doped GaN epilayers synthesized by metal-organic chemical vapor deposition. Applied Physics Letters, 2006, 89, 151903.	1.5	57
90	Photoluminescence studies of band—edge transitions in GaN epitaxial layers grown by plasma—assisted molecular beam epitaxy. Journal of Applied Physics, 1996, 79, 2675-2683.	1.1	56

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91	Comparison of optical transitions in InGaN quantum well structures and microdisks. Journal of Applied Physics, 2001, 89, 4951-4954.	1.1	56
92	Single phase In _x Ga _{1-x} N (0.25 ≤ x ≤ 0.63) alloys synthesized by metal organic chemical vapor deposition. Applied Physics Letters, 2008, 93, .	1.5	56
93	Mechanism of enhanced luminescence in In _x Al _y Ga _{1-x-y} N quaternary alloys. Applied Physics Letters, 2002, 80, 1397-1399.	1.5	55
94	Persistent photoconductivity and related critical phenomena in Zn _{0.3} Cd _{0.7} Se. Physical Review B, 1989, 40, 10025-10028.	1.1	53
95	Kinetics of persistent photoconductivity in Al _{0.3} Ga _{0.7} As and Zn _{0.3} Cd _{0.7} Se semiconductor alloys. Physical Review B, 1992, 45, 13996-14004.	1.1	53
96	Characterization of AlN metal-semiconductor-metal diodes in the spectral range of 440–360nm: Photoemission assessments. Applied Physics Letters, 2008, 92, .	1.5	53
97	Suppression of thermal conductivity in In _x Ga _{1-x} N alloys by nanometer-scale disorder. Applied Physics Letters, 2013, 102, 121906.	1.5	53
98	Band structure of superlattice with graded interfaces. Journal of Applied Physics, 1987, 61, 624-628.	1.1	51
99	The origin of 2.78 eV emission and yellow coloration in bulk AlN substrates. Applied Physics Letters, 2009, 95, .	1.5	51
100	Fabrication and characterization of solid-state thermal neutron detectors based on hexagonal boron nitride epilayers. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2014, 748, 84-90.	0.7	51
101	Optical and electrical properties of Mg-doped AlN nanowires grown by molecular beam epitaxy. Applied Physics Letters, 2015, 106, .	1.5	50
102	Optical resonance modes in InGaN/GaN multiple-quantum-well microring cavities. Applied Physics Letters, 1999, 75, 2563-2565.	1.5	49
103	Linewidths of excitonic luminescence transitions in AlGaN alloys. Applied Physics Letters, 2001, 78, 1829-1831.	1.5	49
104	Origin of the significantly enhanced optical transitions in layered boron nitride. Physical Review B, 2012, 86, .	1.1	49
105	Hexagonal boron nitride thin film thermal neutron detectors with high energy resolution of the reaction products. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2015, 783, 121-127.	0.7	49
106	Large-Scale Growth of High-Quality Hexagonal Boron Nitride Crystals at Atmospheric Pressure from an Fe–Cr Flux. Crystal Growth and Design, 2017, 17, 4932-4935.	1.4	49
107	Optical properties of GaN pyramids. Applied Physics Letters, 1999, 74, 1227-1229.	1.5	48
108	Silicon doping dependence of highly conductive n-type Al _{0.7} Ga _{0.3} N. Applied Physics Letters, 2004, 85, 4669-4671.	1.5	48

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109	Annealing of dry etch damage in metallized and bare (-201) Ga ₂ O ₃ . Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	0.6	48
110	Free excitonic transitions in GaN, grown by metal-organic chemical-vapor deposition. Journal of Applied Physics, 1996, 79, 7001-7004.	1.1	47
111	Size dependence of III-nitride microdisk light-emitting diode characteristics. Applied Physics Letters, 2001, 78, 3532-3534.	1.5	47
112	The origins of leaky characteristics of schottky diodes on p-GaN. IEEE Transactions on Electron Devices, 2003, 50, 292-296.	1.6	47
113	Effects of plasma treatment on the Ohmic characteristics of Ti ⁺ ·Al ⁺ ·Ti ⁺ ·Au contacts to n-AlGa _{0.3} N. Applied Physics Letters, 2006, 89, 082109.	1.5	46
114	Nature of optical transitions involving cation vacancies and complexes in AlN and AlGa _{0.3} N. Applied Physics Letters, 2012, 100, .	1.5	46
115	Band-edge transitions in hexagonal boron nitride epilayers. Applied Physics Letters, 2012, 101, 051110.	1.5	46
116	The origins of near band-edge transitions in hexagonal boron nitride epilayers. Applied Physics Letters, 2016, 108, .	1.5	46
117	Ultraviolet photoluminescence from Gd-implanted AlN epilayers. Applied Physics Letters, 2006, 89, 152107.	1.5	45
118	Hybrid AlN/SiC deep ultraviolet Schottky barrier photodetectors. Applied Physics Letters, 2007, 90, 263505.	1.5	45
119	Erbium-doped GaN optical amplifiers operating at 1.54 μm. Applied Physics Letters, 2009, 95, 111109.	1.5	45
120	Dynamics of a band-edge transition in GaN grown by molecular beam epitaxy. Applied Physics Letters, 1995, 66, 3474-3476.	1.5	44
121	Nitride microlens arrays for blue and ultraviolet wavelength applications. Applied Physics Letters, 2003, 82, 3692-3694.	1.5	44
122	AlN avalanche photodetectors. Applied Physics Letters, 2007, 91, .	1.5	44
123	High quality AlN for deep UV photodetectors. Applied Physics Letters, 2009, 95, .	1.5	44
124	Optical polarization in c-plane Al-rich Al _x Ga _{1-x} N single quantum wells. Applied Physics Letters, 2012, 101, 042103.	1.5	44
125	Optical properties of strain-free AlN nanowires grown by molecular beam epitaxy on Si substrates. Applied Physics Letters, 2014, 104, .	1.5	44
126	1.54 μm emitters based on erbium doped InGa _{0.3} N p-i-n junctions. Applied Physics Letters, 2010, 97, .	1.5	43

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127	Hexagonal boron nitride and 6H-SiC heterostructures. Applied Physics Letters, 2013, 102, .	1.5	43
128	Bandgap and exciton binding energies of hexagonal boron nitride probed by photocurrent excitation spectroscopy. Applied Physics Letters, 2016, 109, .	1.5	43
129	Charge storage and persistent photoconductivity in a Cd _{0.5} Se _{0.5} semiconductor alloy. Physical Review B, 1991, 44, 13343-13348.	1.1	42
130	The incorporation of Nickel and Phosphorus dopants into Boron-Carbon alloy thin films. Applied Physics A: Materials Science and Processing, 1998, 67, 335-342.	1.1	42
131	Photoluminescence studies of Si-doped AlN epilayers. Applied Physics Letters, 2003, 83, 2787-2789.	1.5	42
132	Mechanism of enhanced luminescence in In _x Al _y Ga _{1-x-y} N quaternary epilayers. Applied Physics Letters, 2004, 84, 1480-1482.	1.5	42
133	Well-width dependence of the quantum efficiencies of GaN/Al _x Ga _{1-x} N multiple quantum wells. Applied Physics Letters, 2000, 76, 3040-3042.	1.5	41
134	Ultraviolet photoluminescence from ferromagnetic Fe-doped AlN nanorods. Applied Physics Letters, 2007, 90, 193118.	1.5	41
135	Excitation dynamics of the 1.54 μ m emission in Er doped GaN synthesized by metal organic chemical vapor deposition. Applied Physics Letters, 2007, 90, 051110.	1.5	41
136	Electrical transport properties of Si-doped hexagonal boron nitride epilayers. AIP Advances, 2013, 3, .	0.6	41
137	Excitonic luminescence linewidths in AlGaN alloys with high aluminum concentrations. Applied Physics Letters, 2002, 80, 2907-2909.	1.5	40
138	Evolution of phase separation in In-rich InGaN alloys. Applied Physics Letters, 2010, 96, .	1.5	40
139	Origin of background electron concentration in In _x Al _y Ga _{1-x-y} N alloys. Physical Review B, 2011, 84, .	1.1	40
140	Hexagonal boron nitride neutron detectors with high detection efficiencies. Journal of Applied Physics, 2018, 123, .	1.1	40
141	Persistent photoconductivity in II ^{-VI} and III ^{-V} semiconductor alloys and a novel infrared detector. Journal of Applied Physics, 1991, 69, 6701-6703.	1.1	39
142	Photoresponsivity of ultraviolet detectors based on In _x Al _y Ga _{1-x-y} N quaternary alloys. Applied Physics Letters, 2000, 77, 791-793.	1.5	38
143	Effects of the wave function localization in AlInGaN quaternary alloys. Applied Physics Letters, 2007, 91, 061125.	1.5	38
144	Layer-structured hexagonal (BN)C semiconductor alloys with tunable optical and electrical properties. Journal of Applied Physics, 2014, 115, .	1.1	38

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145	Cluster size and composition variations in yellow and red light-emitting InGaN thin films upon thermal annealing. Journal of Applied Physics, 2004, 95, 5388-5396.	1.1	37
146	High mobility InN epilayers grown on AlN epilayer templates. Applied Physics Letters, 2008, 92, .	1.5	37
147	Origin and roles of oxygen impurities in hexagonal boron nitride epilayers. Applied Physics Letters, 2018, 112, .	1.5	37
148	Optical properties of GaN/AlGaIn multiple quantum well microdisks. Applied Physics Letters, 1997, 71, 2898-2900.	1.5	36
149	Unintentionally doped n-type Al _{0.67} Ga _{0.33} N epilayers. Applied Physics Letters, 2005, 86, 261902.	1.5	36
150	Si-doped high Al-content AlGaIn epilayers with improved quality and conductivity using indium as a surfactant. Applied Physics Letters, 2008, 92, .	1.5	36
151	Probing carbon impurities in hexagonal boron nitride epilayers. Applied Physics Letters, 2017, 110, .	1.5	36
152	Investigation of radiative tunneling in GaN/InGaIn single quantum well light-emitting diodes. Solid-State Electronics, 2002, 46, 2291-2294.	0.8	35
153	Correlation between biaxial stress and free exciton transition in AlN epilayers. Applied Physics Letters, 2007, 91, 121117.	1.5	35
154	A Simplified Method of Making Flexible Blue LEDs on a Plastic Substrate. IEEE Photonics Journal, 2015, 7, 1-7.	1.0	35
155	Relaxation of stored charge carriers in aZn _{0.3} Cd _{0.7} Se mixed crystal. Physical Review B, 1990, 41, 5178-5187.	1.1	34
156	Effective mass of two-dimensional electron gas in an Al _{0.2} Ga _{0.8} N/GaN heterojunction. Applied Physics Letters, 2001, 79, 66-68.	1.5	34
157	Optical properties of the nitrogen vacancy in AlN epilayers. Applied Physics Letters, 2004, 84, 1090-1092.	1.5	33
158	III-nitride-based planar lightwave circuits for long wavelength optical communications. IEEE Journal of Quantum Electronics, 2005, 41, 100-110.	1.0	33
159	Determination of energy-band offsets between GaN and AlN using excitonic luminescence transition in AlGaIn alloys. Journal of Applied Physics, 2006, 99, 013705.	1.1	33
160	Growth and photoluminescence studies of Zn-doped AlN epilayers. Applied Physics Letters, 2006, 89, 192111.	1.5	33
161	Characterization of bulk hexagonal boron nitride single crystals grown by the metal flux technique. Journal of Crystal Growth, 2014, 403, 110-113.	0.7	33
162	Effects of persistent photoconductivity on the characteristic performance of an AlGaIn/GaN heterostructure ultraviolet detector. Applied Physics Letters, 1998, 72, 2868-2870.	1.5	32

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163	AlGa _N ^x GaN _{1-x} AlN quantum-well field-effect transistors with highly resistive AlN epilayers. Applied Physics Letters, 2006, 88, 073513.	1.5	32
164	Optical transitions in Pr-implanted GaN. Applied Physics Letters, 1999, 75, 790-792.	1.5	31
165	Time-resolved photoluminescence studies of an ionized donor-bound exciton in GaN. Applied Physics Letters, 1999, 74, 513-515.	1.5	31
166	Growth and photoluminescence studies of Al-rich Al _N ^x Al _{1-x} GaN quantum wells. Applied Physics Letters, 2006, 89, 131922.	1.5	31
167	Toward achieving flexible and high sensitivity hexagonal boron nitride neutron detectors. Applied Physics Letters, 2017, 111, .	1.5	31
168	Effects of tensile, compressive, and zero strain on localized states in AlInGaN/InGaN quantum-well structures. Applied Physics Letters, 2002, 80, 3099-3101.	1.5	30
169	Temperature-dependent photoluminescence and electron field emission properties of AlN nanotip arrays. Applied Physics Letters, 2009, 94, .	1.5	30
170	Thermoelectric Properties of In _{0.3} Ga _{0.7} N Alloys. Journal of Electronic Materials, 2009, 38, 1132-1135.	1.0	30
171	Growth and deep ultraviolet picosecond time-resolved photoluminescence studies of AlN/GaN multiple quantum wells. Applied Physics Letters, 2001, 78, 3690-3692.	1.5	29
172	Realizing InGaN monolithic solar-photoelectrochemical cells for artificial photosynthesis. Applied Physics Letters, 2014, 104, .	1.5	29
173	Optical and magnetic behavior of erbium-doped GaN epilayers grown by metal-organic chemical vapor deposition. Applied Physics Letters, 2007, 91, .	1.5	28
174	Photoluminescence properties of AlN homoepilayers with different orientations. Applied Physics Letters, 2008, 93, .	1.5	28
175	Charge carrier transport properties in layer structured hexagonal boron nitride. AIP Advances, 2014, 4, .	0.6	28
176	Acceptor-bound exciton recombination dynamics in p-type GaN. Applied Physics Letters, 1995, 67, 3295-3297.	1.5	27
177	Synthesis and properties of Cd _{1-x} Mn _x S diluted magnetic semiconductor ultrafine particles. Journal of Magnetism and Magnetic Materials, 1997, 169, 289-302.	1.0	27
178	MOCVD growth of GaBN on 6H-SiC (0001) substrates. Journal of Electronic Materials, 2000, 29, 452-456.	1.0	27
179	Full-scale self-emissive blue and green microdisplays based on GaN micro-LED arrays. Proceedings of SPIE, 2012, , .	0.8	27
180	High efficiency hexagonal boron nitride neutron detectors with 1%cm ² detection areas. Applied Physics Letters, 2020, 116, .	1.5	27

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181	Two-dimensional electron gas in AlGaIn/GaN heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 1117.	1.6	26
182	Collective effects of interface roughness and alloy disorder in In _x Ga _{1-x} N/GaN multiple quantum wells. Applied Physics Letters, 1998, 73, 1724-1726.	1.5	26
183	Mg acceptor level in InN epilayers probed by photoluminescence. Applied Physics Letters, 2007, 91, .	1.5	26
184	Mode spacing anomaly in InGaIn blue lasers. Applied Physics Letters, 1999, 74, 1066-1068.	1.5	25
185	Thermal annealing effects on an InGaIn film with an average indium mole fraction of 0.31. Applied Physics Letters, 2003, 83, 3906-3908.	1.5	25
186	Enhancing erbium emission by strain engineering in GaN heteroepitaxial layers. Applied Physics Letters, 2010, 96, .	1.5	25
187	Dry etching techniques for active devices based on hexagonal boron nitride epilayers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, 061517.	0.9	25
188	Growth and device processing of hexagonal boron nitride epilayers for thermal neutron and deep ultraviolet detectors. AIP Advances, 2016, 6, .	0.6	25
189	Dynamics of exciton transfer between the bound and the continuum states in GaAs-Al _x Ga _{1-x} As multiple quantum wells. Physical Review B, 1990, 41, 12949-12952.	1.1	24
190	Three-step growth method for high quality AlN epilayers. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 126-129.	0.8	24
191	Layer number dependent optical properties of multilayer hexagonal BN epilayers. Applied Physics Letters, 2017, 110, .	1.5	24
192	Localized vibrational modes of carbon-hydrogen complexes in GaN. Applied Physics Letters, 1999, 75, 659-661.	1.5	23
193	Transition metal ion implantation into AlGaIn. Journal of Applied Physics, 2003, 94, 4956.	1.1	23
194	Current-injected 1.54 μ m light emitting diodes based on erbium-doped GaN. Applied Physics Letters, 2008, 93, 033502.	1.5	23
195	Probing exciton-phonon interaction in AlN epilayers by photoluminescence. Applied Physics Letters, 2009, 95, .	1.5	23
196	Excitation mechanisms of Er optical centers in GaN epilayers. Applied Physics Letters, 2015, 107, 171105.	1.5	23
197	Optical enhancement of room temperature ferromagnetism in Er-doped GaN epilayers. Applied Physics Letters, 2009, 95, 022510.	1.5	22
198	Electrical transport properties of (BN)-rich hexagonal (BN)C semiconductor alloys. AIP Advances, 2014, 4, 087141.	0.6	21

#	ARTICLE	IF	CITATIONS
199	High sensitivity hexagonal boron nitride lateral neutron detectors. Applied Physics Letters, 2019, 114, .	1.5	21
200	Quantum-confined Stark effects in CdS 1D quantum dots. Physical Review B, 1995, 51, 5457-5460.	1.1	20
201	Thermally stable Schottky contacts on n-type GaN using ZrB ₂ . Applied Physics Letters, 2006, 88, 183505.	1.5	20
202	Surface chemical and electronic properties of plasma-treated n-type Al _{0.5} Ga _{0.5} N. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 3410-3416.	0.8	20
203	Effects of double layer AlN buffer layers on properties of Si-doped Al _x Ga _{1-x} N for improved performance of deep ultraviolet light emitting diodes. Journal of Applied Physics, 2013, 113, 123501.	1.1	20
204	Effects of Mg-doped AlN/AlGaN superlattices on properties of p-GaN contact layer and performance of deep ultraviolet light emitting diodes. AIP Advances, 2014, 4, 047122.	0.6	20
205	Crystal field analysis of rare-earth ions energy levels in GaN. Optical Materials, 2014, 37, 165-174.	1.7	20
206	Carbon-rich hexagonal (BN)C alloys. Journal of Applied Physics, 2015, 117, .	1.1	20
207	Fabrication and optical studies of AlGaN/GaN quantum-well waveguides. Applied Physics Letters, 2001, 79, 12-14.	1.5	19
208	Quantum well intermixing in GaInNAs/GaAs structures. Journal of Applied Physics, 2003, 94, 7581.	1.1	19
209	III-Nitride Quantum Devices in Microphotronics. Critical Reviews in Solid State and Materials Sciences, 2003, 28, 131-183.	6.8	19
210	Growth and photoluminescence studies of a-plane Al _x Ga _{1-x} N quantum wells. Applied Physics Letters, 2007, 90, 221105.	1.5	19
211	Probing the relationship between structural and optical properties of Si-doped AlN. Applied Physics Letters, 2010, 96, 131906.	1.5	19
212	High quality AlN grown on double layer AlN buffers on SiC substrate for deep ultraviolet photodetectors. Applied Physics Letters, 2012, 101, .	1.5	19
213	Dynamics of exciton localization in a CdSe _{0.5} Si _{0.5} mixed crystal. Physical Review B, 1990, 42, 7284-7287.	1.1	18
214	Acceptor-bound exciton transition in Mg-doped AlN epilayer. Applied Physics Letters, 2004, 85, 2271-2273.	1.5	18
215	Sublimation growth of aluminum nitride crystals. Journal of Crystal Growth, 2006, 297, 105-110.	0.7	18
216	Nature of exciton transitions in hexagonal boron nitride. Applied Physics Letters, 2016, 108, .	1.5	18

#	ARTICLE	IF	CITATIONS
217	Superlattice with multiple layers per period. <i>Physical Review B</i> , 1986, 33, 5851-5853.	1.1	17
218	Growth and optical studies of two-dimensional electron gas of Al-rich AlGaIn/GaN heterostructures. <i>Applied Physics Letters</i> , 2002, 81, 1809-1811.	1.5	17
219	Strong green luminescence in quaternary InAlGaIn thin films. <i>Applied Physics Letters</i> , 2003, 82, 1377-1379.	1.5	17
220	Time-resolved electroluminescence studies of III-nitride ultraviolet photonic-crystal light-emitting diodes. <i>Applied Physics Letters</i> , 2004, 85, 2104-2106.	1.5	17
221	Carrier lifetime in erbium-doped GaN waveguide emitting in 1540 nm wavelength. <i>Applied Physics Letters</i> , 2010, 97, 241105.	1.5	17
222	SiO ₂ /TiO ₂ distributed Bragg reflector near 1.5 μ m fabricated by e-beam evaporation. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2013, 31, .	0.9	17
223	Correlation between the optical loss and crystalline quality in erbium-doped GaN optical waveguides. <i>Applied Optics</i> , 2013, 52, 5426.	0.9	16
224	Room-Temperature Lasing Action in GaN Quantum Wells in the Infrared 1.5 μ m Region. <i>ACS Photonics</i> , 2018, 5, 1303-1309.	3.2	16
225	Lateral charge carrier transport properties of B-10 enriched hexagonal BN thick epilayers. <i>Applied Physics Letters</i> , 2019, 115, 072108.	1.5	16
226	Band-tail states in aZn _{0.3} Cd _{0.7} Se semiconductor alloy probed by persistent photoconductivity. <i>Physical Review B</i> , 1992, 45, 4520-4523.	1.1	15
227	Persistent photoconductivity inZn _{0.04} Cd _{0.96} Te semiconductor thin films. <i>Physical Review B</i> , 1993, 48, 8145-8151.	1.1	15
228	Optical properties of a high-quality insulating GaN epilayer. <i>Applied Physics Letters</i> , 1999, 74, 3821-3823.	1.5	15
229	Effects of alloy disorder on the transport properties of Al _x Ga _{1-x} N epilayers probed by persistent photoconductivity. <i>Applied Physics Letters</i> , 2000, 76, 1728-1730.	1.5	15
230	Beryllium acceptor binding energy in AlN. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	15
231	Low-temperature epitaxial growth and photoluminescence characterization of GaN. <i>Applied Physics Letters</i> , 1994, 65, 2317-2319.	1.5	14
232	Barrier-width dependence of quantum efficiencies of GaN/Al _x Ga _{1-x} N multiple quantum wells. <i>Applied Physics Letters</i> , 2000, 77, 1170-1172.	1.5	14
233	Propagation properties of light in AlGaIn/GaN quantum-well waveguides. <i>Applied Physics Letters</i> , 2001, 79, 2511-2513.	1.5	14
234	Delta-doped AlGaIn/GaN metal-oxide-semiconductor heterostructure field-effect transistors with high breakdown voltages. <i>Applied Physics Letters</i> , 2002, 81, 4649-4651.	1.5	14

#	ARTICLE	IF	CITATIONS
235	Persistent photoconductivity in $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ quaternary alloys. Applied Physics Letters, 2003, 82, 1884-1886.	1.5	14
236	Spectroscopic studies of Er-centers in MOCVD grown GaN layers highly doped with Er. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 193-195.	1.7	14
237	Semiconducting hexagonal boron nitride for deep ultraviolet photonics. Proceedings of SPIE, 2012, , .	0.8	14
238	Temperature dependence of the energy bandgap of two-dimensional hexagonal boron nitride probed by excitonic photoluminescence. Journal of Applied Physics, 2014, 115, 053503.	1.1	14
239	Toward the realization of erbium-doped GaN bulk crystals as a gain medium for high energy lasers. Applied Physics Letters, 2016, 109, .	1.5	14
240	Effects of electron mass anisotropy on Hall factors in $6\text{H}\text{-SiC}$. Applied Physics Letters, 1996, 68, 1341-1343.	1.5	13
241	Plasma heating in highly excited GaN/AlGa multiple quantum wells. Applied Physics Letters, 1998, 73, 2476-2478.	1.5	13
242	Formation and dissolution of microcrystalline graphite in carbon-implanted GaN. Journal of Applied Physics, 2000, 88, 5662-5665.	1.1	13
243	Optimizing growth conditions for GaN/AlGa multiple quantum well structures. Applied Physics Letters, 2000, 76, 864-866.	1.5	13
244	Bulk AlN crystal growth by direct heating of the source using microwaves. Journal of Crystal Growth, 2004, 262, 168-174.	0.7	13
245	AlN MSM and Schottky photodetectors. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2148-2151.	0.8	13
246	Photonic properties of erbium doped InGaN alloys grown on Si (001) substrates. Applied Physics Letters, 2011, 98, 081102.	1.5	13
247	Dramatic enhancement of $1.54\ \mu\text{m}$ emission in Er doped GaN quantum well structures. Applied Physics Letters, 2015, 106, 121106.	1.5	13
248	Effects of surface recombination on the charge collection in h-BN neutron detectors. Journal of Applied Physics, 2019, 125, 104501.	1.1	13
249	Dynamics of localized excitons in InGaN/GaN quantum wells. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2215.	1.6	12
250	Enhanced magnetization in erbium doped GaN thin films due to strain induced electric fields. Applied Physics Letters, 2011, 99, 122506.	1.5	12
251	Surfactant effects of gallium on quality of AlN epilayers grown via metal-organic chemical-vapour deposition on SiC substrates. Journal Physics D: Applied Physics, 2012, 45, 285103.	1.3	12
252	Formation energy of optically active Er^{3+} centers in Er doped GaN. Applied Physics Letters, 2012, 101, 051114.	1.5	12

#	ARTICLE	IF	CITATIONS
253	Optical excitation cross section of erbium in GaN. Applied Optics, 2013, 52, 1132.	0.9	12
254	Synthesis and properties of Cd/sub 1-x/Mn/sub x/S diluted magnetic semiconductor nanoparticles. IEEE Transactions on Magnetics, 1994, 30, 4930-4932.	1.2	11
255	Evidence for bistable defects in 6H-SiC. Solid State Communications, 1994, 89, 995-998.	0.9	11
256	Emission and absorption cross-sections of an Er:GaN waveguide prepared with metal organic chemical vapor deposition. Applied Physics Letters, 2011, 99, .	1.5	11
257	Electric-field-enhanced persistent photoconductivity in aZn0.02Cd0.98Te semiconductor alloy. Physical Review B, 1992, 46, 3810-3816.	1.1	10
258	Deep ultraviolet photoluminescence studies of AlN photonic crystals. Applied Physics Letters, 2006, 88, 133113.	1.5	10
259	Growth and fabrication of GaN/Er:GaN/GaN core-cladding planar waveguides. Applied Physics Letters, 2019, 114, 222105.	1.5	10
260	Anisotropic index of refraction and structural properties of hexagonal boron nitride epilayers probed by spectroscopic ellipsometry. Journal of Applied Physics, 2020, 127, .	1.1	10
261	High-Quality Al-Rich AlGaIn Alloys. Springer Series in Materials Science, 2012, , 29-81.	0.4	10
262	Temperature dependence of the energy bandgap of multi-layer hexagonal boron nitride. Applied Physics Letters, 2017, 111, 132106.	1.5	10
263	Semiconductor superlattices with periodic disorder. Journal of Applied Physics, 1988, 63, 1984-1989.	1.1	9
264	Optical transitions in InGaN/AlGaIn single quantum wells. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 1139.	1.6	9
265	Studies of field-induced nonequilibrium electron transport in an In _x Ga _{1-x} N (x=0.6) epilayer grown on GaN. Applied Physics Letters, 2003, 82, 1413-1415.	1.5	9
266	Valence band structure of AlN probed by photoluminescence. Applied Physics Letters, 2008, 92, 041114.	1.5	9
267	Near infrared photonic devices based on Er-doped GaN and InGaIn. Optical Materials, 2011, 33, 1066-1070.	1.7	9
268	Effects of growth pressure on erbium doped GaN infrared emitters synthesized by metal organic chemical vapor deposition. Optical Materials Express, 2012, 2, 1095.	1.6	9
269	Refractive index of erbium doped GaN thin films. Applied Physics Letters, 2014, 105, 081104.	1.5	9
270	Photoluminescence quantum efficiency of Er optical centers in GaN epilayers. Scientific Reports, 2017, 7, 39997.	1.6	9

#	ARTICLE	IF	CITATIONS
271	Precession of Kepler's orbit. American Journal of Physics, 1985, 53, 694-695.	0.3	8
272	DX centers in Al _{0.34} Ga _{0.66} As amorphous thin films. Solid State Communications, 1993, 87, 787-790.	0.9	8
273	Near-field optical study of AlGaN/GaN quantum-well waveguide. Applied Physics Letters, 2004, 84, 1832-1834.	1.5	8
274	Optical properties of GaN/AlN multiple quantum wells. Solid State Communications, 2004, 131, 389-392.	0.9	8
275	Higher lying conduction band in GaN and AlN probed by photoluminescence spectroscopy. Applied Physics Letters, 2006, 88, 261919.	1.5	8
276	Deep ultraviolet photoluminescence of Tm-doped AlGaN alloys. Applied Physics Letters, 2009, 94, 111103.	1.5	8
277	Enhancement of 1.5- μ m emission under 980-nm resonant excitation in Er and Yb co-doped GaN epilayers. Applied Physics Letters, 2016, 109, .	1.5	8
278	Hyperspectral Nonlinear Optical Light Generation from a Monolithic GaN Microcavity. Advanced Optical Materials, 2017, 5, 1600804.	3.6	8
279	Boron nitride neutron detector with the ability for detecting both thermal and fast neutrons. Applied Physics Letters, 2022, 120, .	1.5	8
280	Metal-insulator transition in semiconductor alloys probed by persistent photoconductivity. Physical Review B, 1995, 51, 4132-4136.	1.1	7
281	Observation of electronic Raman scattering from Mg-doped wurtzite GaN. Applied Physics Letters, 2000, 76, 2889-2891.	1.5	7
282	Annealing behavior of luminescence from erbium-implanted GaN films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 127-131.	1.7	7
283	Birefringence of GaN/AlGaN optical waveguides. Applied Physics Letters, 2003, 83, 1698-1700.	1.5	7
284	Free nucleation of aluminum nitride single crystals in HPBN crucible by sublimation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 117, 99-104.	1.7	7
285	Erbium doped GaN synthesized by hydride vapor-phase epitaxy. Optical Materials Express, 2015, 5, 596.	1.6	7
286	Excitation and emission mechanisms of Er:GaN gain medium in 1.5- μ m region. Applied Physics Letters, 2017, 111, .	1.5	7
287	Optical properties of GaN/Er:GaN/GaN core-cladding planar waveguides. Applied Physics Express, 2019, 12, 075505.	1.1	7
288	Probing the surface oxidation process in hexagonal boron nitride epilayers. AIP Advances, 2020, 10, 025213.	0.6	7

#	ARTICLE	IF	CITATIONS
289	Charge collection in h-BN neutron detectors at elevated temperatures. Applied Physics Letters, 2021, 118, 092102.	1.5	7
290	Band structure of a periodic potential with two wells and two barriers per period. American Journal of Physics, 1987, 55, 462-465.	0.3	6
291	Optical Transitions and Recombination Lifetimes in GaN and InGaN Epilayers, and InGaN/GaN and GaN/AlGaN Multiple Quantum Wells. Materials Research Society Symposia Proceedings, 1996, 449, 829.	0.1	6
292	Surface emission of In _x Ga _{1-x} N epilayers under strong optical excitation. Applied Physics Letters, 1997, 70, 984-986.	1.5	6
293	Achieving conductive high Al-content AlGa _N alloys for deep UV photonics. , 2007, 6479, 265.		6
294	Er-Doped GaN and In _x Ga _{1-x} N for Optical Communications. Topics in Applied Physics, 2010, , 115-157.	0.4	6
295	Optical and magneto-optical properties of erbium doped InGa _N and Ga _N epilayers. Optical Materials, 2011, 33, 1059-1062.	1.7	6
296	Excitation cross section of erbium-doped Ga _N waveguides under 980-nm optical pumping. Applied Physics Letters, 2014, 105, 051106.	1.5	6
297	Direct detection of rare earth ion distributions in gallium nitride and its influence on growth morphology. Journal of Applied Physics, 2020, 127, 013102.	1.1	6
298	Band structure of non-ideal semiconductor superlattices. Superlattices and Microstructures, 1987, 3, 689-695.	1.4	5
299	Disorder and persistent photoconductivity in Zn _x Cd _{1-x} Se semiconductor alloys. Physical Review B, 1996, 54, 1471-1473.	1.1	5
300	Optical properties of Pr implanted Ga _N epilayers and Al Ga _{1-x} N alloys. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 167-170.	1.7	5
301	Epitaxial growth and time-resolved photoluminescence studies of AlN epilayers. , 2003, 4992, 202.		5
302	Deep bandtail states picosecond intensity-dependent carrier dynamics of Ga _N epilayer under high excitation. Applied Physics B: Lasers and Optics, 2005, 80, 521-526.	1.1	5
303	Photoluminescence properties of erbium doped InGa _N epilayers. Applied Physics Letters, 2009, 95, 041113.	1.5	5
304	Metal-semiconductor-metal neutron detectors based on hexagonal boron nitride epitaxial layers. Proceedings of SPIE, 2012, , .	0.8	5
305	Resonant excitation cross-sections of erbium in freestanding Ga _N bulk crystals. Applied Physics Letters, 2018, 112, .	1.5	5
306	Critical thickness of hexagonal GaBN/BN heterostructures. Journal of Applied Physics, 2019, 125, .	1.1	5

#	ARTICLE	IF	CITATIONS
307	Band structure and infrared optical transitions in ErN. Applied Physics Letters, 2020, 116, 171104.	1.5	5
308	Electrical transport properties of hexagonal boron nitride epilayers. Semiconductors and Semimetals, 2021, 107, 393-454.	0.4	5
309	Direct observation of edge luminescence excited by long-lived-exciton-polariton propagation in CdS. Physical Review B, 1989, 40, 1385-1387.	1.1	4
310	Structure and spin-glass properties of Cd/sub 0.5/Mn/sub 0.5/S diluted magnetic semiconductor quantum dots. IEEE Transactions on Magnetics, 1995, 31, 3761-3763.	1.2	4
311	X-ray diffraction analysis of the defect structure in Al _x Ga _{1-x} N films grown by metalorganic chemical vapor deposition. Journal of Materials Science, 2004, 39, 1853-1855.	1.7	4
312	Time-Resolved Photoluminescence Studies of Indium-Rich InGaN Alloys. Chinese Physics Letters, 2005, 22, 472-474.	1.3	4
313	Metastable Giant Moments in Gd-Implanted GaN, Si, and Sapphire. Journal of Superconductivity and Novel Magnetism, 2011, 24, 2123-2128.	0.8	4
314	Optoelectronic properties of hexagonal boron nitride epilayers. Proceedings of SPIE, 2013, , .	0.8	4
315	Probing of local alloy disorder in InGaN using Er ³⁺ ions. Optical Materials, 2014, 36, 1730-1733.	1.7	4
316	Current injection 154 Åµm light-emitting devices based on Er-doped GaN/AlGaN multiple quantum wells. Optical Materials Express, 2016, 6, 3476.	1.6	4
317	Synthesis and photoluminescence properties of hexagonal B ₂ GaN alloys and quantum wells. Applied Physics Express, 2019, 12, 011002.	1.1	4
318	Effects of unique band structure of h-BN probed by photocurrent excitation spectroscopy. Applied Physics Express, 2022, 15, 051005.	1.1	4
319	Dynamics of bound-exciton energy transformation to edge-luminescence centers in CdS. Journal of Luminescence, 1990, 45, 251-253.	1.5	3
320	Measurement of the Al mole fraction of bulk AlGa _N and AlGa _N /Ga _N heterostructure by photoconductance method. Journal of Applied Physics, 1999, 86, 2696-2699.	1.1	3
321	Synthesis and optical characterization of erbium-doped III-N double heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 118-121.	1.7	3
322	Non-Equilibrium Acceptor Concentration in GaN:Mg Grown by Metalorganic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 2003, 798, 448.	0.1	3
323	Thermoelectric Properties of Er-doped InGa _N Alloys for High Temperature Applications. Materials Research Society Symposia Proceedings, 2011, 1325, 41.	0.1	3
324	Erbium-doped a-plane Ga _N epilayers synthesized by metal-organic chemical vapor deposition. Optical Materials Express, 2015, 5, 274.	1.6	3

#	ARTICLE	IF	CITATIONS
325	Erbium-doped AlN epilayers synthesized by metal-organic chemical vapor deposition. Optical Materials Express, 2015, 5, 648.	1.6	3
326	Thermal neutron detectors based on hexagonal boron nitride epilayers. , 2016, , .		3
327	Electronic structure and dispersion of compensated n-i-p superlattices with small period lengths. Physical Review B, 1989, 40, 5561-5566.	1.1	2
328	Photoluminescence Properties Of GaN/AlGa _N Multiple Quantum Well Microdisks. Materials Research Society Symposia Proceedings, 1997, 482, 684.	0.1	2
329	Growth and Characterization of B _x Ga _{1-x} N on 6H-SiC (0001) by MOVPE. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	2
330	Growth and Characterization of B _x Ga _{1-x} N on 6H-SiC (0001) by MOCVD. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 429-434.	1.0	2
331	Advances in III-nitride micro-size light emitters. III-Vs Review, 2001, 14, 32-37.	0.1	2
332	Mechanism of photoluminescence in GaN/Al _{0.2} Ga _{0.8} N superlattices. Applied Physics Letters, 2001, 79, 3806-3808.	1.5	2
333	Exciton-polariton propagation in AlGa _N /Ga _N quantum-well waveguides probe by time-resolved photoluminescence. , 2002, , .		2
334	Mg-doped Al-rich AlGa _N alloys for deep UV emitters. , 2004, , .		2
335	GaN Light-Emitting Triodes for High-Efficiency Hole Injection. Journal of the Electrochemical Society, 2006, 153, C734.	1.3	2
336	Expanding into blue and green. Nature Photonics, 2011, 5, 521-522.	15.6	2
337	Response of alpha particles in hexagonal boron nitride neutron detectors. Applied Physics Letters, 2017, 110, .	1.5	2
338	Temperature dependence studies of Er optical centers in GaN epilayers grown by MOCVD. MRS Advances, 2017, 2, 135-140.	0.5	2
339	Polarization-resolved Er emission in Er doped GaN bulk crystals. Journal of Applied Physics, 2020, 127, 243107.	1.1	2
340	Band structure and ultraviolet optical transitions in ErN. Applied Physics Letters, 2021, 118, .	1.5	2
341	Development of nitride microLEDs and displays. Semiconductors and Semimetals, 2021, , 1-56.	0.4	2
342	High-efficiency and high-sensitivity thermal neutron detectors based on hexagonal BN epilayers. , 2017, , .		2

#	ARTICLE	IF	CITATIONS
343	Erbium energy levels in GaN grown by hydride vapor phase epitaxy. AIP Advances, 2020, 10, .	0.6	2
344	Persistent photoconductivity in Cd _{0.7} Zn _{0.3} Se mixed crystals. Journal of Luminescence, 1990, 45, 198-200.	1.5	1
345	Persistent Photoconductivity in p-Type GaN Epilayers and n-Type AlGa _{1-x} N/GaN Heterostructures. Materials Research Society Symposia Proceedings, 1996, 449, 537.	0.1	1
346	Transient characteristics of Al _x Ga _{1-x} N/GaN heterojunction field-effect transistors. Applied Physics Letters, 2000, 77, 4046-4048.	1.5	1
347	<title>Growth and optoelectronic properties of III-nitride quaternary alloys</title>. , 2001, 4280, 27.		1
348	Advances in III-nitride micro-photonic devices. , 0, , .		1
349	III-Nitride Photonic Crystals for Blue and UV Emitters. Materials Research Society Symposia Proceedings, 2003, 798, 424.	0.1	1
350	III-nitride ultraviolet photonic materials: epitaxial growth, optical and electrical properties, and applications. , 2003, , .		1
351	Field-induced non-equilibrium electron transport in an In _{0.4} Ga _{0.6} N epilayer grown on GaN studied by subpicosecond Raman spectroscopy. Semiconductor Science and Technology, 2004, 19, S427-S429.	1.0	1
352	III-nitride blue and UV photonic-crystal light-emitting diodes. , 2004, , .		1
353	Carrier dynamics in AlN and GaN epilayers at the elevated temperatures. , 2005, , .		1
354	Comment on "Spectral identification of thin film coated and solid form semiconductor neutron detectors" by McGregor and Shultis. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2005, 536, 228-231.	0.7	1
355	III-nitride deep ultraviolet micro- and nano-photonics. , 2006, , .		1
356	Growth and optical properties of a-plane AlN and Al rich AlN/Al _x Ga _{1-x} N quantum wells grown on r-plane sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1568-1570.	0.8	1
357	1.54 μm emitter and optical amplifier based on Er doped InGa _{1-x} N/GaN. , 2010, , .		1
358	Erbium-doped GaN bulk crystals as a gain medium for eye-safe high energy lasers. , 2018, , .		1
359	AlN. , 2011, , 21-68.		1
360	Piezoelectric Effects in GaN/AlGa _{1-x} N Multiple Quantum Wells Probed by Picosecond Time-Resolved Photoluminescence. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 130-135.	1.0	1

#	ARTICLE	IF	CITATIONS
361	Charge collection and trapping mechanisms in hexagonal boron nitride epilayers. Applied Physics Letters, 2021, 119, .	1.5	1
362	The ground state of a particle under the influence of a uniformly charged sphere. American Journal of Physics, 1986, 54, 1046-1048.	0.3	0
363	Optical Properties of Mg-GaN, GaN/AlGaN SCH structures, and GaN on ZnO Substrates. Materials Research Society Symposia Proceedings, 1995, 395, 527.	0.1	0
364	Optical transitions and dynamic processes in III-nitride epilayers and multiple quantum wells. , 1997, , .		0
365	Well Thickness And Doping Effects, And Room Temperature emission mechanisms in InGaN/GaN And GaN/AlGaN Multiple Quantum Wells. Materials Research Society Symposia Proceedings, 1997, 482, 678.	0.1	0
366	Dynamics of fundamental optical transitions in group III nitrides. , 1998, , .		0
367	<title>Piezoelectric effects on the dynamics of optical transitions in GaN/AlxGa$1-x$N multiple quantum wells</title>. , 1999, 3624, 198.		0
368	Correlation between Sheet Carrier Density-Mobility Product and Persistent Photoconductivity in ALGAN/GAN Modulation Doped Heterostructures. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	0
369	Time-Resolved Photoluminescence Studies of In _x Ga _{1-x} As _{1-y} N _y . Materials Research Society Symposia Proceedings, 1999, 607, 153.	0.1	0
370	Optical properties of III-nitride microcavities. , 1999, , .		0
371	<title>Exciton localization dynamics in Al _x Ga _{1-x} N alloys</title>. , 2000, 3940, 139.		0
372	Fabrication and Characterization of In _x Al _y Ga _{1-x-y} N Ultraviolet Detectors. Materials Research Society Symposia Proceedings, 2000, 639, 1071.	0.1	0
373	Time-resolved photoluminescence studies of Al-rich AlGa _N alloys. , 2002, , .		0
374	AlGa _N /Ga _N Metal-Oxide-Semiconductor Heterostructure Field-Effect Transistors (MOSHFETs) with the Delta-Doped Barrier Layer. Materials Research Society Symposia Proceedings, 2002, 743, L9.11.1.	0.1	0
375	Optical resonant modes in InGa _N MQW/Ga _N micro-cone. Current Applied Physics, 2002, 2, 383-387.	1.1	0
376	Compositional changes in erbium-implanted Ga _N films due to annealing. Journal of Electronic Materials, 2003, 32, 382-387.	1.0	0
377	Thermal annealing effects on the optical properties of high-indium InGa _N epi-layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2654-2657.	0.8	0
378	Delta-doped AlGa _N /Ga _N Heterostructure Field-Effect Transistors with Incorporation of AlN Epilayers. Materials Research Society Symposia Proceedings, 2003, 798, 102.	0.1	0

#	ARTICLE	IF	CITATIONS
379	Defect Reduction in Al _x Ga _{1-x} N Films Grown by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2003, 42, 1231-1232.	0.8	0
380	Time-resolved photoluminescence studies of Si- and Mg-doped AlN epilayers. , 2004, , .		0
381	Optical Reflectance of Bulk AlN Crystals and AlN Epitaxial Films. AIP Conference Proceedings, 2005, , .	0.3	0
382	Visible and Infrared Emission from Er-doped III-N Light Emitting Diodes. Materials Research Society Symposia Proceedings, 2005, 866, 76.	0.1	0
383	III-Nitride Wide Bandgap Semiconductors for Optical Communications. , 2006, , .		0
384	Al rich AlN/AlGa _N Quantum Wells. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
385	Erbium-doped GaN epilayers synthesized by metal-organic chemical vapor deposition. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
386	Time-resolved photoluminescence studies of Mg-doped AlN epilayers. , 2006, , .		0
387	Investigation of The Electrical and Chemical Properties of Plasma-Treated AlGa _N . Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
388	Achieving p-In _x Ga _{1-x} N alloys with high In contents. , 2010, , .		0
389	III-nitride nanostructures for energy generation. , 2010, , .		0
390	Impurities and conductivity control in Al-rich AlGa _N alloys. , 2011, , .		0
391	Optical and magneto-optical properties of neodymium and erbium doped gallium nitride epilayers. , 2011, , .		0
392	p-Type AlN nanowires and AlN nanowire light emitting diodes on Si. , 2015, , .		0
393	Hexagonal boron nitride for deep UV photonics. , 2015, , .		0
394	Optical excitation of Er centers in GaN epilayers grown by MOCVD. , 2016, , .		0
395	Hexagonal boron nitride epilayers for deep UV photonics. , 2017, , .		0
396	Development of Micro-LEDs and Applications. , 2019, , .		0

#	ARTICLE	IF	CITATIONS
397	Correlation Between Sheet Carrier Density-Mobility Product and Persistent Photoconductivity in AlGaIn/GaN Modulation Doped Heterostructures. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 626-632.	1.0	0
398	<title>Optimizing GaN/AlGaIn multiple quantum well structures by time-resolved photoluminescence</title>. , 2001, , .		0
399	Current Injection Emitters at 1.54 Åµm Based on Erbium Doped GaN p-i-n Structures. , 2012, , .		0
400	Rare Earth doped GaN for photonic devices. , 2017, , .		0
401	Telecommunication-Wavelength Lasing in Er-doped GaN Multiple Quantum Wells at Room Temperature. , 2018, , .		0
402	Formation energy and optical excitation mechanisms of Er in GaN semi-bulk crystals. Applied Physics Letters, 2022, 120, 052103.	1.5	0
403	Effects of polarization field on optical transitions and selection rules in Er doped GaN. Optical Materials Express, 0, , .	1.6	0
404	A conductive AFM study of carbon-rich hexagonal (BN)C semiconductor alloys. MRS Communications, 0, , 1.	0.8	0